



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

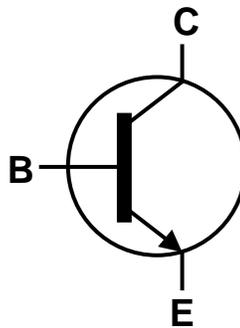
- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Complementary PNP Type: NK- MMBT4403

Mechanical Data

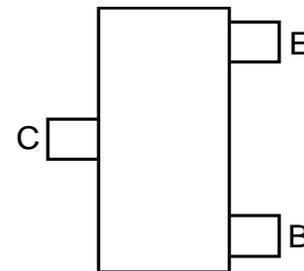
- Package: SOT23
- Package material: molded Plastic "Green" Compound
UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per
MIL-STD-202, Method 208 
- Weight: 0.008 grams (Approximate)



Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$ unless otherwise specified)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	600	mA
Peak Collector Current	I_{CM}	1	A
Peak Base Current	I_{BM}	200	mA

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$ unless otherwise specified)

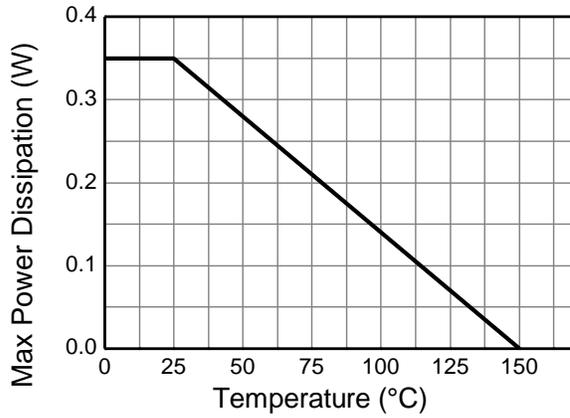
Characteristic	Symbol	Value	Unit
Power Dissipation	P_D	(Note 5) 310	mW
		(Note 6) 350	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	(Note 5) 403	$^\circ\text{C/W}$
		(Note 6) 357	
Thermal Resistance, Junction to Leads	$R_{\theta JL}$	350	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	120	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

ESD Ratings (Note 8)

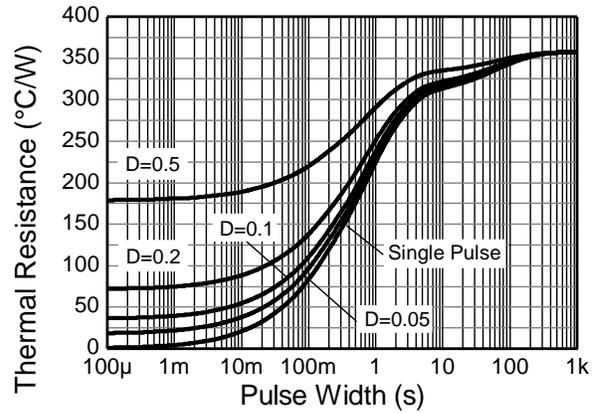
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
- For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 - Same as note (5), except the device is mounted on 15 mm x 15mm 1oz copper.
 - Thermal resistance from junction to solder-point (at the end of the leads).
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

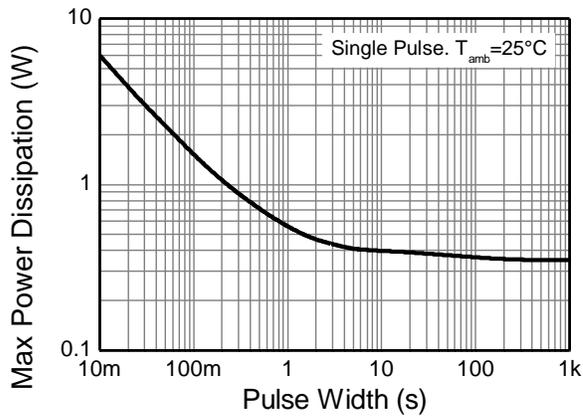
Thermal Characteristics and Derating Information



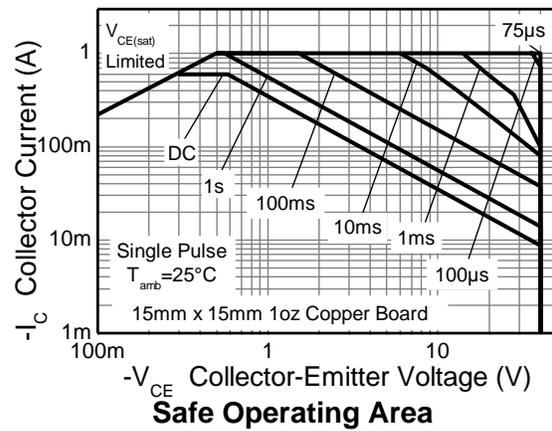
Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation



Safe Operating Area

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$ unless otherwise specified)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV_{CBO}	60	—	V	$I_C = 100\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage(Note 9)	BV_{CEO}	40	—	V	$I_C = 10.0\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	6.0	—	V	$I_E = 100\mu\text{A}, I_C = 0$
Collector Cutoff Current	I_{CEX}	—	100	nA	$V_{CE} = 35\text{V}, V_{EB(off)} = 0.4\text{V}$
Base Cutoff Current	I_{BL}	—	100	nA	$V_{CE} = 35\text{V}, V_{EB(off)} = 0.4\text{V}$
ON CHARACTERISTICS (Note 9)					
DC Current Gain	h_{FE}	20	—	—	$I_C = 100\mu\text{A}, V_{CE} = 1.0\text{V}$ $I_C = 1.0\text{mA}, V_{CE} = 1.0\text{V}$ $I_C = 10\text{mA}, V_{CE} = 1.0\text{V}$ $I_C = 150\text{mA}, V_{CE} = 1.0\text{V}$ $I_C = 500\text{mA}, V_{CE} = 2.0\text{V}$
		40	—		
		80	—		
		100	300		
		40	—		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	0.40 0.75	V	$I_C = 150\text{mA}, I_B = 15\text{mA}$ $I_C = 500\text{mA}, I_B = 50\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	0.75 —	0.95 1.2	V	$I_C = 150\text{mA}, I_B = 15\text{mA}$ $I_C = 500\text{mA}, I_B = 50\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{cb}	—	6.5	pF	$V_{CB} = 5.0\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	C_{eb}	—	30	pF	$V_{EB} = 0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$
Input Impedance	h_{ie}	1.0	15	k Ω	$V_{CE} = 10\text{V}, I_C = 1.0\text{mA},$ $f = 1.0\text{kHz}$
Voltage Feedback Ratio	h_{re}	0.1	8.0	$\times 10^{-4}$	
Small Signal Current Gain	h_{fe}	40	500	—	
Output Admittance	h_{oe}	1.0	30	μS	
Current Gain-Bandwidth Product	f_T	250	—	MHz	
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	15	ns	$V_{CC} = 30\text{V}, I_C = 150\text{mA},$ $V_{BE(off)} = 2.0\text{V}, I_{B1} = 15\text{mA}$
Rise Time	t_r	—	20	ns	
Storage Time	t_s	—	225	ns	$V_{CC} = 30\text{V}, I_C = 150\text{mA},$ $I_{B1} = -I_{B2} = 15\text{mA}$
Fall Time	t_f	—	30	ns	

 Note: 9. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

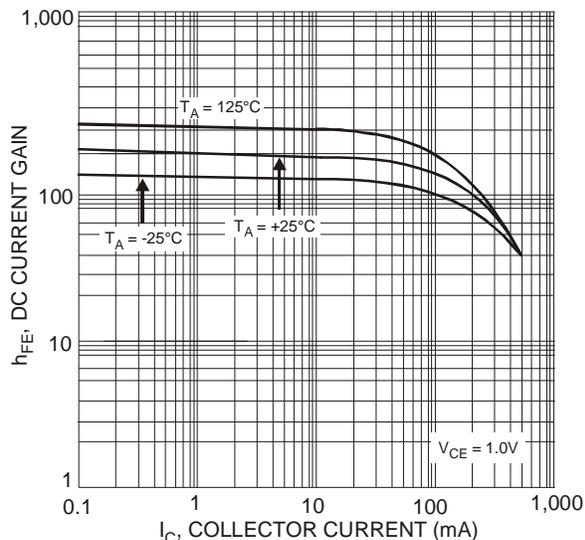


Figure 1 Typical DC Current Gain vs. Collector Current

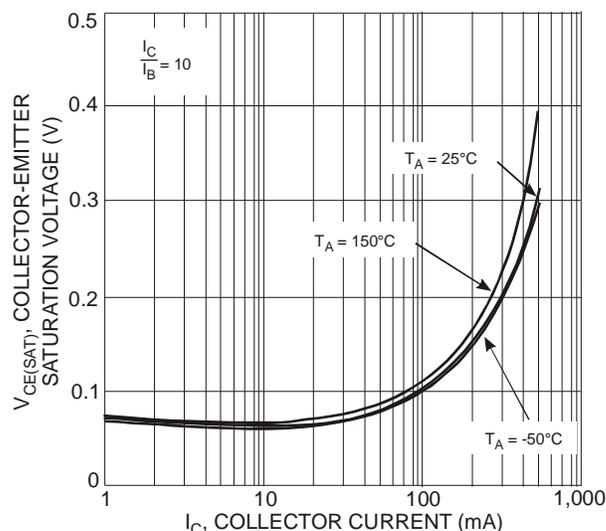


Figure 2 Collector-Emitter Saturation Voltage vs. Collector Current

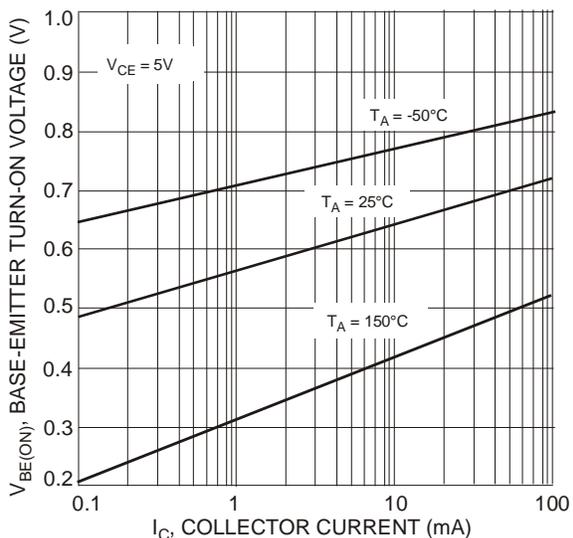


Figure 3 Typical Base-Emitter Turn-On Voltage vs. Collector Current

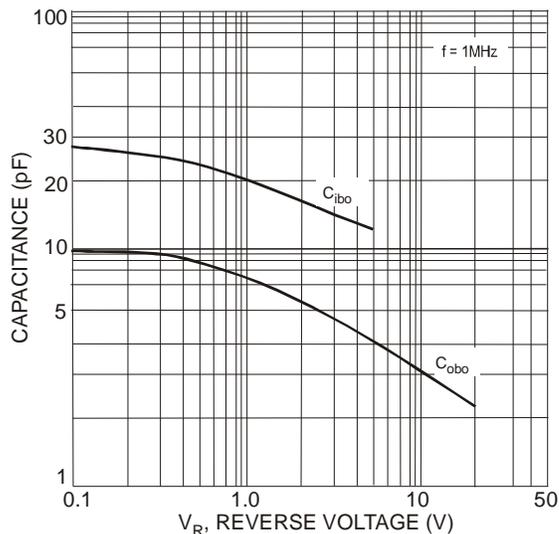


Figure 4 Typical Capacitance Characteristics

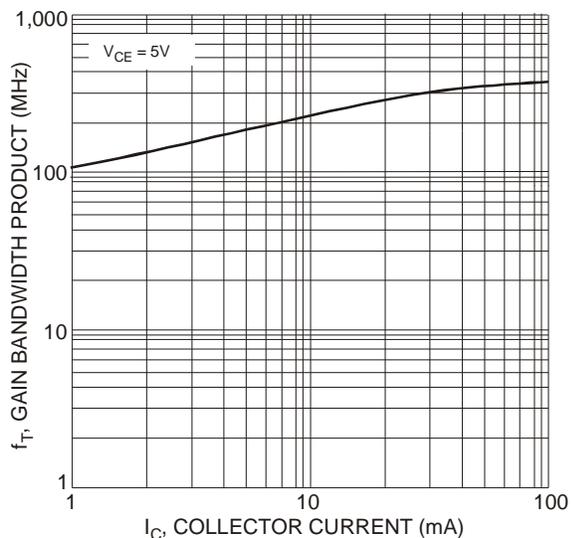


Figure 5 Typical Gain Bandwidth Product vs. Collector Current

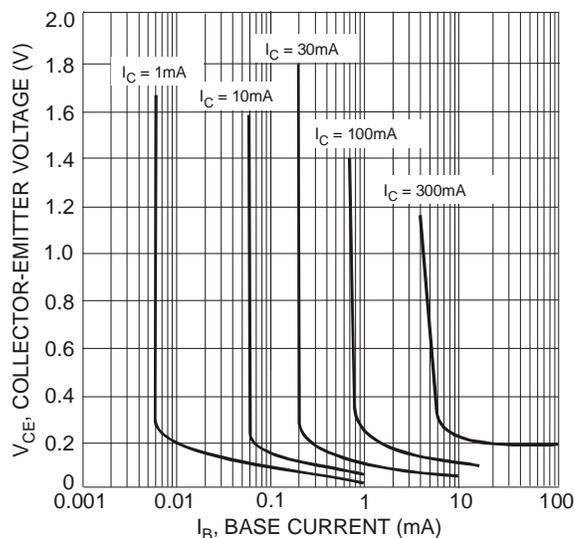
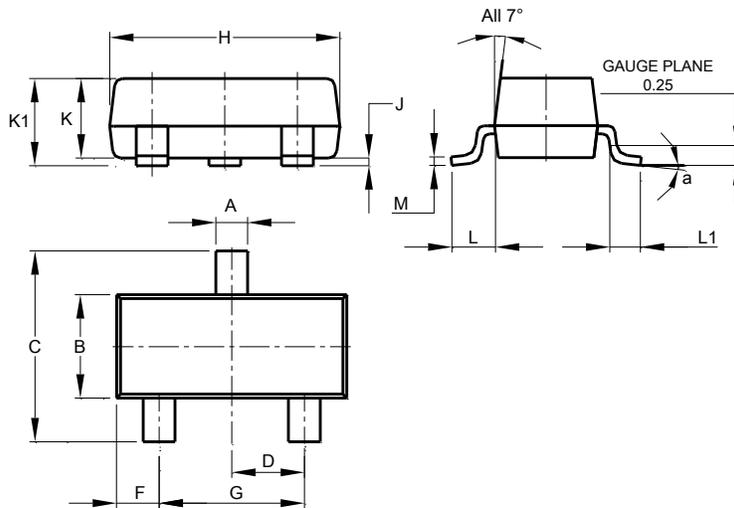


Figure 6 Typical Collector Saturation Region

Package Outline Dimensions

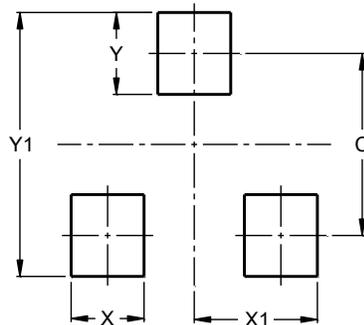
SOT23



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9